PBSS2540MB

40 V, 0.5 A NPN low VCEsat (BISS) transistor Rev. 1 — 4 April 2012

Product data sheet

1. **Product profile**

1.1 General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS3540MB.

1.2 Features and benefits

- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Low collector-emitter saturation voltage V_{CFsat}
- High collector current capability I_C and I_{CM}
- High efficiency due to less heat generation
- AEC-Q101 qualified
- Reduced Printed-Circuit Board (PCB) requirements

1.3 Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger

- LCD backlighting
- Drivers in low supply voltage applications (e.g. lamps and LEDs)

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	40	V
I _C	collector current		-	-	500	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	1	Α
R _{CEsat}	collector-emitter saturation resistance	$I_C = 500$ mA; $I_B = 50$ mA; pulsed; $t_p \le 300$ µs; $\delta \le 0.02$; $T_{amb} = 25$ °C	-	380	500	mΩ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	Е	emitter	1	3
3	С	collector	2	1—
			Transparent top view	 2
			SOT883B (DFN1006B-3)	sym021

3. Ordering information

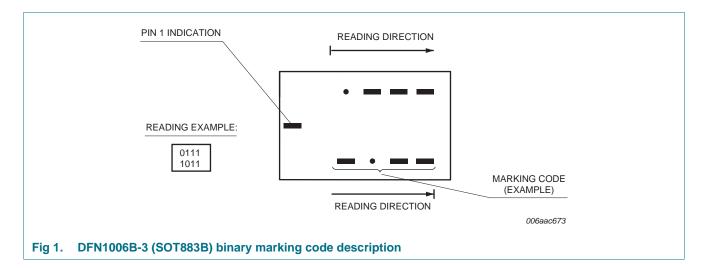
Table 3. Ordering information

Type number	number Package				
	Name	Description	Version		
PBSS2540MB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B		

4. Marking

Table 4. Marking codes

Type number	Marking code
PBSS2540MB	0001 0010



5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	40	V
V_{CEO}	collector-emitter voltage	open base		-	40	V
V_{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	500	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	1	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1][2]	-	250	mW
			[3][2]	-	590	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

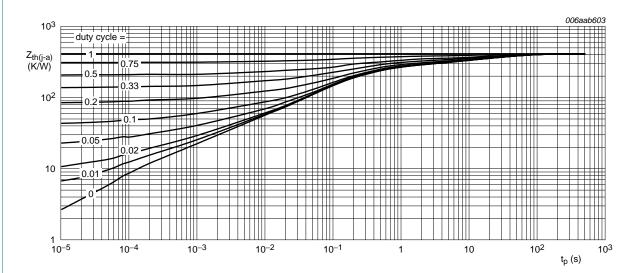
^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

6. Thermal characteristics

Table 6. Thermal characteristics

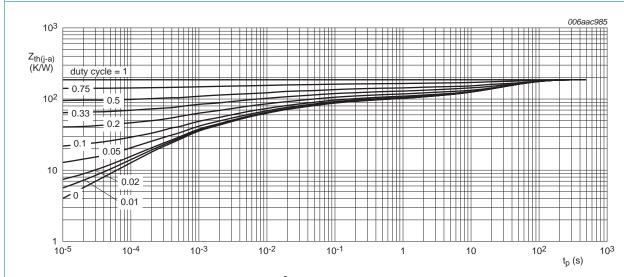
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance	in free air	[1][2]	-	-	500	K/W
	from junction to ambient		[3][2]	-	-	212	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².



FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



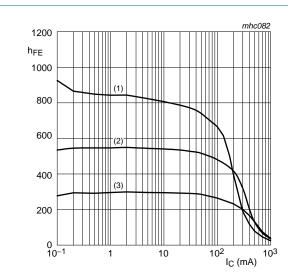
FR4 PCB, mounting pad for collector 1 cm²

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{CBO}	collector-base cut-off	$V_{CB} = 30 \text{ V; } I_{E} = 0 \text{ A; } T_{amb} = 25 ^{\circ}\text{C}$	-	-	100	nΑ
	current	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 2 V; I_{C} = 10 mA; T_{amb} = 25 °C	200	-	-	
		V_{CE} = 2 V; I_{C} = 100 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02 ; T_{amb} = 25 °C	150	-	-	
		V_{CE} = 2 V; I_{C} = 500 mA; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	50	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 10 mA; I_B = 0.5 mA; T_{amb} = 25 °C	-	-	50	mV
		I_C = 100 mA; I_B = 5 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	100	mV
		$I_C = 200 \text{ mA}; I_B = 10 \text{ mA}; \text{ pulsed}; \\ t_p \le 300 \mu\text{s}; \delta \le 0.02 ; T_{amb} = 25 ^{\circ}\text{C}$	-	-	200	mV
		I_C = 500 mA; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	250	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 500 mA; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	380	500	mΩ
V_{BEsat}	base-emitter saturation voltage	I_C = 500 mA; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 100 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02 ; T_{amb} = 25 °C	-	-	1.1	V
f⊤	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 100 \text{ mA; } f = 100 \text{ MHz;}$ $T_{amb} = 25 \text{ °C}$	250	450	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$	-	-	6	pF



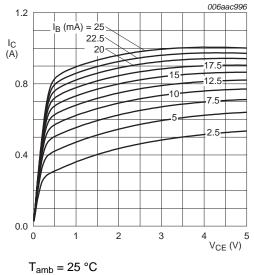
$$V_{CE} = 2 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

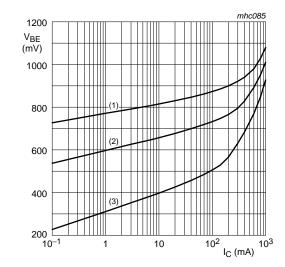
(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55$$
 °C

DC current gain as a function of collector Fig 4. current; typical values



Collector current as a function of Fig 5. collector-emitter voltage; typical values



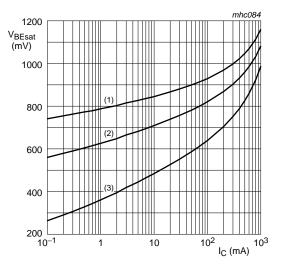
 $V_{CE} = 2 V$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Base-emitter voltage as a function of collector Fig 6. current; typical values



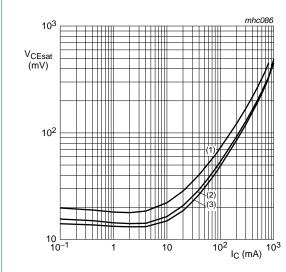
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 7. Base-emitter saturation voltage as a function of collector current; typical values



$$I_C/I_B = 20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values

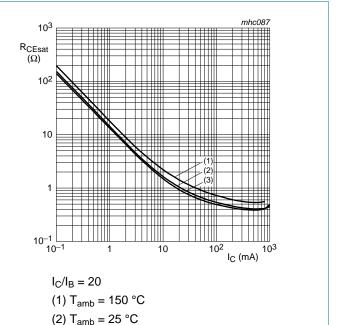


Fig 9. Collector-emitter saturation resistance as a function of collector current; typical values

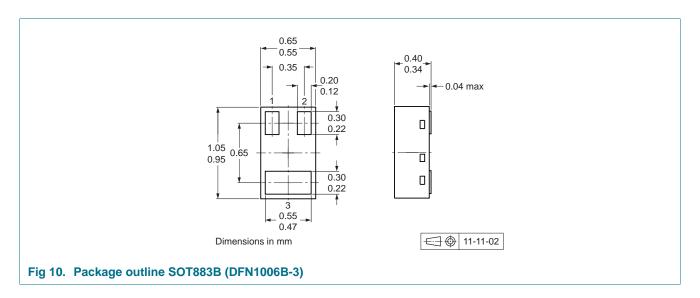
(3) $T_{amb} = -55 \, ^{\circ}C$

8. Test information

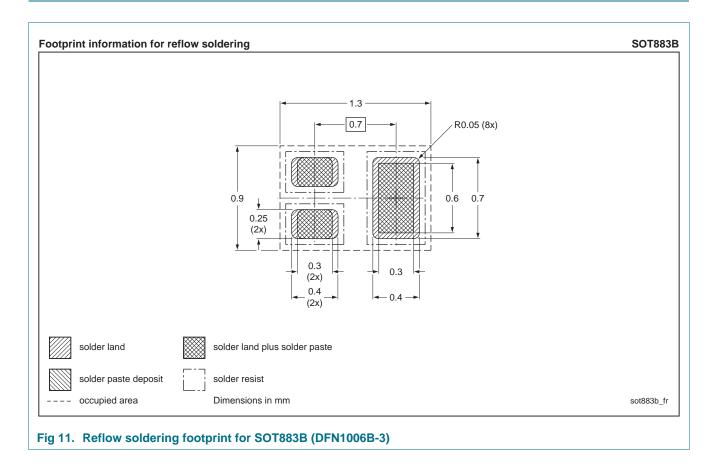
8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline



10. Soldering





11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS2540MB v.1	20120404	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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40 V, 0.5 A NPN low VCEsat (BISS) transistor

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